Appl. No. 09/653,149

REMARKS

Claims 1-25 and 34-75 are pending in the application with claims 43 and 44

amended and new claims 48-75 added herein. No new matter is being presented in

this application.

This Request for Continued Examination (RCE) Application is also being filed in

an abundance of caution to permit consideration of a Supplemental Information

Disclosure Statement.

Further, Applicant herewith submits copies of the Information Disclosure Statement

and Form PTO-1449 filed on October 8, 2001 and July 1, 2002. No initialed copies of the

Form PTO-1449 have been received back from the Examiner. To the extent that the

submitted references listed on the copies of Form PTO-1449 have not already been

considered, and the copies have not been initialed, such examination and initialing is

requested at this time, as well as return of a copy of each initialed Form PTO-1449 to the

undersigned.

Respectfully submitted,

Dated: 22 Oct 2002

Reg. No. 44,854



Application Serial No	
Filing Date	August 31, 2000
Inventor	Garo J. Derderian, et al
Assignee	Micron Technology, Inc.
Group Art Unit	2818
Examiner	T. Le
Attorney's Docket No	Ml22-1330
Title: Capacitor Fabrication Methods and Capacitor Constructions	

VERSION WITH MARKINGS TO SHOW CHANGES MADE ACCOMPANYING PRELIMINARY AMENDMENT ACCOMPANYING A RCE FILING

In the Claims

The claims have been amended as follows. <u>Underlines</u> indicate insertions and <u>strikeouts</u> indicate deletions.

- 43. (amended) The method of claim 40 wherein the atomic layer deposited conductive material layer is formed on the first electrode, further comprising chemisorbing additional alternating first and second precursor layers before forming the dielectric layer.
- 44. (amended) The method of claim 40 wherein the atomic layer deposited conductive material layer comprises elemental metal, a metal alloy, or a metal: containing compound.

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